

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	6	"6,014,030"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 10:25
S2	929	324/713	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 10:32
S3	757	361/93:1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 09:30
S4	4442	current adj (sense sensing) adj resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 09:21
S5	178	current adj (sense sensing) near (MOS MOSFET FET field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 09:22
S6	0	current adj (sense sensing) near (MOS MOSFET FET field adj effect) near switch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 09:23
S7	36	current adj (sense sensing) near (MOS MOSFET FET field adj effect) same switch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:29
S8	4	"5,986,441"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:24
S9	5	("4914542" "5004970" "5008586" "5164659" "5220207").PN.	USPAT	OR	ON	2004/08/31 11:15
S10	10	"5,805,434"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:26

S11	3	"6,282,107"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:28
S12	12	("4975821" "5126931" "5331533" "5374857" "5434768" "5734563" "5774350" "5805434" "5812383" "5814884" "5886383" "5973939").PN.	USPAT	OR	ON	2004/08/31 11:26
S13	12	("4975821" "5126931" "5331533" "5374857" "5434768" "5734563" "5774350" "5805434" "5812383" "5814884" "5886383" "5973939").PN.	USPAT	OR	ON	2004/08/31 11:27
S14	12	("4975821" "5126931" "5331533" "5374857" "5434768" "5734563" "5774350" "5805434" "5812383" "5814884" "5886383" "5973939").PN.	USPAT	OR	ON	2004/08/31 11:27
S15	2179645	current adj (sense sensing) near across (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:30
S16	3	current adj (sense sensing) near across adj (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 11:42
S17	14	over adj current same voltage adj across adj (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:07
S18	14	over adj current same voltage near across adj (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:11
S19	5	("4479083" "4502000" "4502001" "4949028" "4967136").PN.	USPAT	OR	ON	2004/08/31 12:09
S20	22	"5528122".URPN.	USPAT	OR	ON	2004/08/31 12:10
S21	22	"5528122".URPN.	USPAT	OR	ON	2004/08/31 12:10

S22	130	over adj current and voltage near across adj (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:11
S23	92	over adj current and voltage near across adj (MOS MOSFET FET field adj effect switch) and temperature adj	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:12
S24	11	over adj current and voltage near across adj (MOS MOSFET FET field adj effect switch) same temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:27
S25	5	over adj current and voltage near across adj (MOS MOSFET FET field adj effect switch) and temperature adj (sense sensing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 12:35
S26	1	over adj current and voltage near across adj (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:15
S27	4	("5530335" "5554919" "5721480" "5736832").PN.	USPAT	OR	ON	2004/08/31 12:54
S28	3	"6014030".URPN.	USPAT	OR	ON	2004/08/31 12:56
S29	3	"6014030":URPN.	USPAT	OR	ON	2004/08/31 12:56
S30	5	over adj current and voltage near (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:34
S31	106644	voltage adj across (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:34
S32	14	voltage adj across adj (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:37
S33	0	voltage adj across adj (MOS MOSFET FET field adj effect switch) same temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:38

S34	502	temperature adj (compensate compensating) adj resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:39
S35	0	temperature adj (compensate compensating) adj resistor same operational adj amplifier same voltage adj drop near (MOS FET MOSFET field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:40
S36	0	temperature adj (compensate compensating) adj resistor same voltage adj drop near (MOS FET MOSFET field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:40
S37	0	temperature adj (compensate compensating) adj resistor and voltage adj drop near (MOS FET MOSFET field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 13:41
S38	40	temperature adj (compensate compensating) adj resistor same operational adj amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 15:57
S39	17	temperature adj (compensate compensating) adj resistor same current adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 16:03
S40	20	temperature adj (compensate compensating) near resistor same current adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 16:25
S41	354	324/705	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/31 16:25
S42	187	current adj (limit limiting) and switch near across near voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:48
S43	95	current adj (limit limiting) and switch near across near voltage and (MOS MOSFET field adj effect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:48

S44	28	current adj (limit limiting) and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj divider	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:49
S45	28	current adj (limit limiting) and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:54
S46	0	current adj (limit limiting) near transistor and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:55
S47	0	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:56
S48	8	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:57
S49	53	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 15:58
S50	1	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across near (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 16:02
S51	3	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across near (MOS MOSFET field adj effect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2004/12/06 16:04
S52	900	361/93.1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/23 13:01

S53	196	361/93.7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/23 16:31
S54	429	324/705	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/26 10:19
S55	1024	324/713	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/01/26 10:52